

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

524,288 WORDS × 8 BIT STATIC RAM

DESCRIPTION

The TC554001FL/FTL is a 4,194,304-bit static random access memory (SRAM) organized as 524,288 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 3.0 to 5.5V power supply. Advanced circuit technology provides both high speed and low power at an operating current of 10mA/MHz(typ) and minimum cycle time of 70 ns. It is automatically placed in low-power mode at 60 μ A standby current (max) when chip enable ($\overline{CE}$) is asserted high. There are two control inputs. $\overline{CE}$ is used to select the device and for data retention control, and output enable ($\overline{OE}$) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. The TC554001FL/FTL is available in a standard plastic 32-pin small-outline package(SOP) and 32-pin thin-small-outline package(TSOP).

FEATURES

- Low-power dissipation
Operating: 55 mW/MHz (typical)
- Standby current of 8 μ A (maximum) at $T_a = 25^\circ\text{C}$
- Single power supply voltage of 3.0 to 5.5 V
- Power down features using $\overline{CE}$
- Data retention supply voltage of 2.0 to 5.5 V
- Direct TTL compatibility for all inputs and outputs

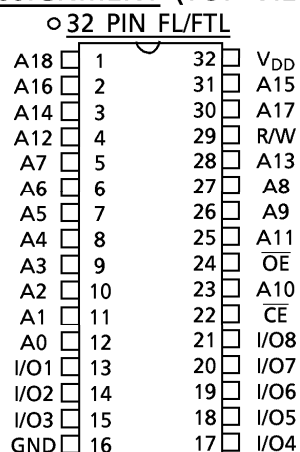
- Access Time (maximum)

	5 V $\pm$ 10%			3.0 to 5.5 V
	-70 V	-85 V	-10 V	-70 V/85 V/-10 V
Access Time	70 ns	85 ns	100 ns	150 ns
$\overline{CE}$ Access Time	70 ns	85 ns	100 ns	150 ns
$\overline{OE}$ Access Time	35 ns	45 ns	50 ns	75 ns

- Package:

SOP32-P-525-1.27 (FL) (Weight: 1.14 g typ)
TSOP II 32-P-400-1.27 (FTL) (Weight: 0.51 g typ)

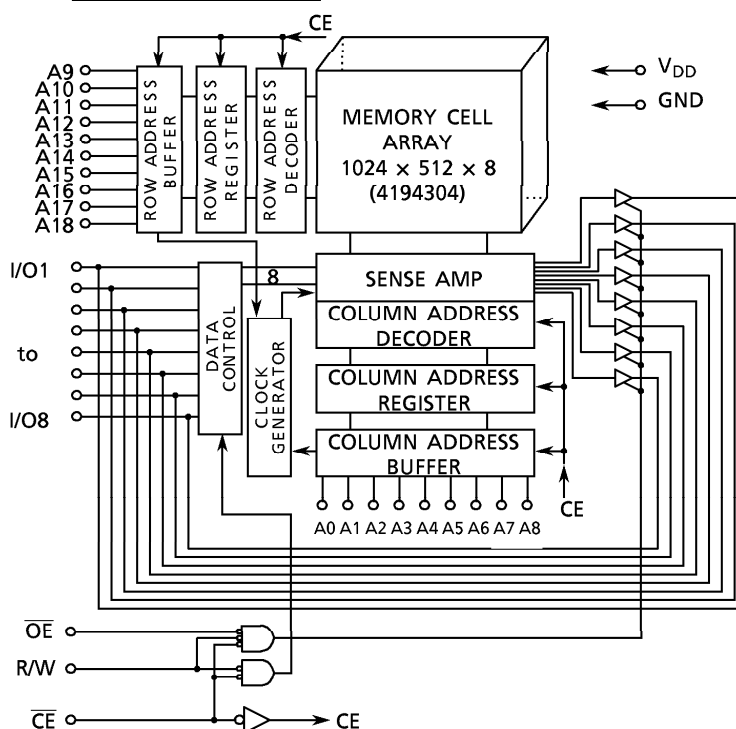
PIN ASSIGNMENT (TOP VIEW)



PIN NAMES

A0 to A18	Address Inputs
R/W	Read/Write Control
$\overline{OE}$	Output Enable
$\overline{CE}$	Chip Enable
I/O1 to I/O8	Data Input/Output
V _{DD}	Power
GND	Ground

BLOCK DIAGRAM



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OPERATION MODE

OPERATION MODE	$\overline{CE}$	$\overline{OE}$	R/W	I/O1 to I/O8	POWER
Read	L	L	H	D _{OUT}	I _{DDO}
Write	L	x	L	D _{IN}	I _{DDO}
Output Disabled	L	H	H	High-Z	I _{DDO}
Standby	H	x	x	High-Z	I _{DDS}

Note: x = don't care. H=logic high. L=logic low.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V _{DD}	Power Supply Voltage	- 0.3 to 7.0	V
V _{IN}	Input Voltage	- 0.3* to 7.0	V
V _{I/O}	Input and Output Voltage	- 0.5 to V _{DD} + 0.5	V
P _D	Power Dissipation	0.6	W
T _{solder}	Soldering Temperature (10 s)	260	°C
T _{strg.}	Storage Temperature	- 55 to 150	°C
T _{opr.}	Operating Temperature	0 to 70	°C

* - 3.0 V when measured at a pulse width of 50 ns

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	5 V ± 10%			3.0 to 5.5			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
V _{DD}	Power Supply Voltage	4.5	5.0	5.5	3.0	5.0	5.5	V
V _{IH}	Input High Voltage	2.2	-	V _{DD} + 0.3	V _{DD} - 0.2	-	V _{DD} + 0.3	V
V _{IL}	Input Low Voltage	- 0.3*	-	0.8	- 0.3*	-	0.2	V
V _{DH}	Data Retention Supply Voltage	2.0	-	5.5	2.0	-	5.5	V

* - 3.0 V when measured at a pulse width of 50 ns

DC CHARACTERISTICS ($T_a = 0^\circ$ to 70°C , $V_{DD} = 5\text{ V} \pm 10\%$)

SYMBOL	PARAMETER	TEST CONDITION			MIN	TYP	MAX	UNIT	
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}			–	–	± 1.0	μA	
I _{LO}	Output Leakage Current	CE = V _{IH} or OE = V _{IH} or R/W = V _{IL} V _{OUT} = 0 V to V _{DD}			–	–	± 1.0	μA	
I _{OH}	Output High Current	V _{OH} = 2.4 V			– 1.0	–	–	mA	
I _{OL}	Output Low Current	V _{OL} = 0.4 V			2.1	–	–	mA	
I _{DDO1}	Operating Current	CE = V _{IL} and R/W = V _{IH} I _{OUT} = 0 mA Other Inputs = V _{IH} /V _{IL}		Tcycle	min	–	–	80	mA
					1 μs	–	15	–	
I _{DDO2}		CE = 0.2 V and R/W = V _{DD} – 0.2 V I _{OUT} = 0 mA Other Inputs = V _{DD} – 0.2 V/0.2 V		Tcycle	min	–	–	70	mA
					1 μs	–	10	–	
I _{DDS1}	Standby Current	CE = V _{IH}			–	–	3	mA	
I _{DDS2}		CE = V _{DD} – 0.2 V	V _{DD} = 2.0 to 5.5 V	Ta = 25°C	–	4	8	μA	
				Ta = 0° to 70°C	–	–	60		
			V _{DD} = 3.0 V	Ta = 25°C	–	2	–		
				Ta = 0 to 40°C	–	–	6		
				Ta = 0° to 70°C	–	–	30		

DC CHARACTERISTICS ($T_a = 0^\circ$ to 70°C , $V_{DD} = 3.3\text{ V} \pm 0.3\text{ V}$)

SYMBOL	PARAMETER	TEST CONDITION			MIN	TYP	MAX	UNIT
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}			–	–	± 1.0	μA
I _{LO}	Output Leakage Current	CE̅ = V _{IH} or OE̅ = V _{IH} or R/W = V _{IL} V _{OUT} = 0 V to V _{DD}			–	–	± 1.0	μA
I _{OH}	Output High Current	V _{OH} = V _{DD} –0.2 V			– 0.1	–	–	mA
I _{OL}	Output Low Current	V _{OL} = 0.2 V			0.1	–	–	mA
I _{DDO2}	Operating Current	CE̅ = 0.2 V and R/W = V _{DD} –0.2 V I _{OUT} = 0 mA Other Inputs = V _{DD} –0.2 V/0.2 V	Tcycle	min	–	–	35	mA
				1 μs	–	5	–	
I _{DDS2}	Standby Current	CE̅ = V _{DD} –0.2 V	V _{DD} = 3.3 ± 0.3 V	Ta = 25°C	–	2	4	μA
				Ta = 0° to 70°C	–	–	40	
			V _{DD} = 3.3 V	Ta = 25°C	–	2	–	
				Ta = 0 to 40°C	–	–	8	
				Ta = 0° to 70°C	–	–	35	

CAPACITANCE ($T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	$V_{IN} = \text{GND}$	10	pF
C_{OUT}	Output Capacitance	$V_{OUT} = \text{GND}$	10	pF

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS AND OPERATING CONDITIONS ($T_a = 0^\circ$ to 70°C , $V_{DD} = 5\text{ V} \pm 10\%$)

READ CYCLE

SYMBOL	PARAMETER	TC554001FL/FTL						UNIT
		-70 V		-85 V		-10 V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	70	–	85	–	100	–	ns
t _{ACC}	Address Access Time	–	70	–	85	–	100	
t _{CO}	Chip Enable Accses Time	–	70	–	85	–	100	
t _{OE}	Output Enable Accses Time	–	35	–	45	–	50	
t _{COE}	Chip Enable Low to Output Active	10	–	10	–	10	–	
t _{OEE}	Output Enable Low to Output Active	5	–	5	–	5	–	
t _{OD}	Chip Enable Hige to Output High-Z	–	25	–	30	–	35	
t _{ODO}	Output Enable Hige to Output High-Z	–	25	–	30	–	35	
t _{OH}	Output Data Hold Time	10	–	10	–	10	–	

WRITE CYCLE

SYMBOL	PARAMETER	TC554001FL/FTL						UNIT
		-70 V		-85 V		-10 V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{WC}	Write Cycle Time	70	–	85	–	100	–	ns
t _{WP}	Write Pulse Width	50	–	55	–	60	–	
t _{CW}	Chip Enable to End of Write	60	–	70	–	80	–	
t _{AS}	Address Setup Time	0	–	0	–	0	–	
t _{WR}	Write Recovery Time	0	–	0	–	0	–	
t _{ODW}	R/W Low to Output High-Z	–	25	–	25	–	25	
t _{OEW}	R/W High to Output Active	5	–	5	–	5	–	
t _{DS}	Data Setup Time	30	–	35	–	40	–	
t _{DH}	Data Hold Time	0	–	0	–	0	–	

AC TEST CONDITIONS

Output Load: 30 pF + one TTL gate (-70 V)

100 pF + one TTL gate (-85 V, -10 V)

Input Pulse Level: 0.6 V, 2.4 V

Timing Measurements: 1.5 V

Reference Level: 1.5 V

t_r , t_f : 5 ns

AC CHARACTERISTICS AND OPERATING CONDITIONS(Ta = 0° to 70°C, V_{DD} = 3.0 V to 5.5 V)READ CYCLE

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{RC}	Read Cycle Time	150	—	ns
t _{ACC}	Address Access Time	—	150	
t _{CO}	Chip Enable ($\overline{CE}$) Access Time	—	150	
t _{OE}	Output Enable to Output in Valid	—	75	
t _{COE}	Chip Enable ($\overline{CE}$) to Output in Low-Z	10	—	
t _{OEE}	Output Enable to Output in Low-Z	5	—	
t _{OD}	Chip Enable ($\overline{CE}$) to Output in High-Z	—	50	
t _{ODO}	Output Enable to Output in High-Z	—	50	
t _{OH}	Output Data Hold Time	10	—	

WRITE CYCLE

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{WC}	Write Cycle Time	150	—	ns
t _{WP}	Write Pulse Width	100	—	
t _{CW}	Chip Enable to End of Write	120	—	
t _{AS}	Address Setup Time	0	—	
t _{WR}	Write Recovery Time	0	—	
t _{ODW}	R/W Low to Output High-Z	—	50	
t _{OEW}	R/W Hige to Output Active	5	—	
t _{DS}	Data Setup Time	60	—	
t _{DH}	Data Hold Time	0	—	

AC TEST CONDITIONS

Output Load: 100 pF (Include Jig)

Input Pulse Level: V_{DD} – 0.2 V/0.2 V

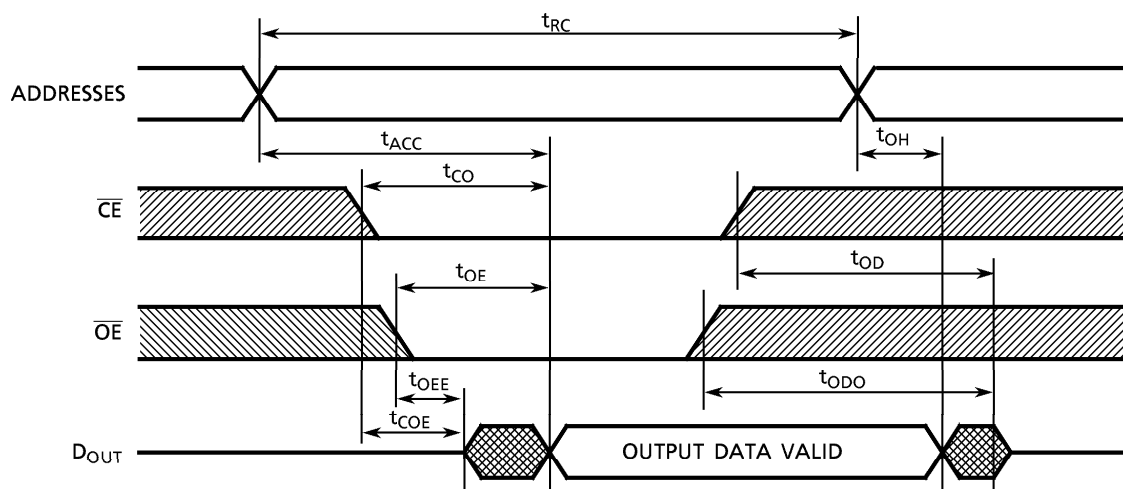
Timing Measurements: 1.5 V

Reference Level: 1.5 V

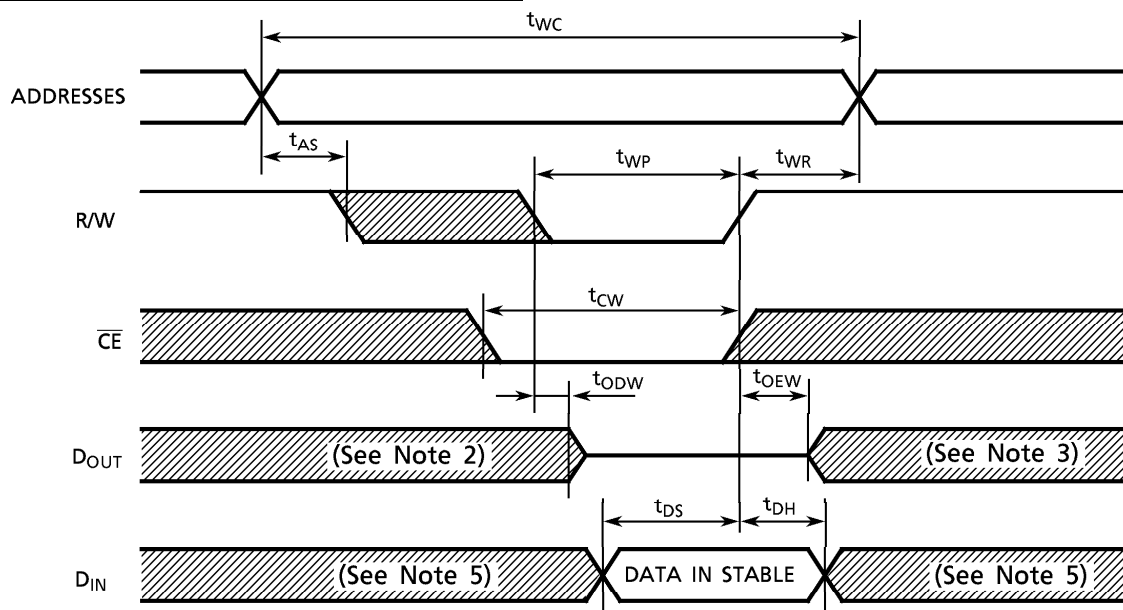
t_r, t_f : 5 ns

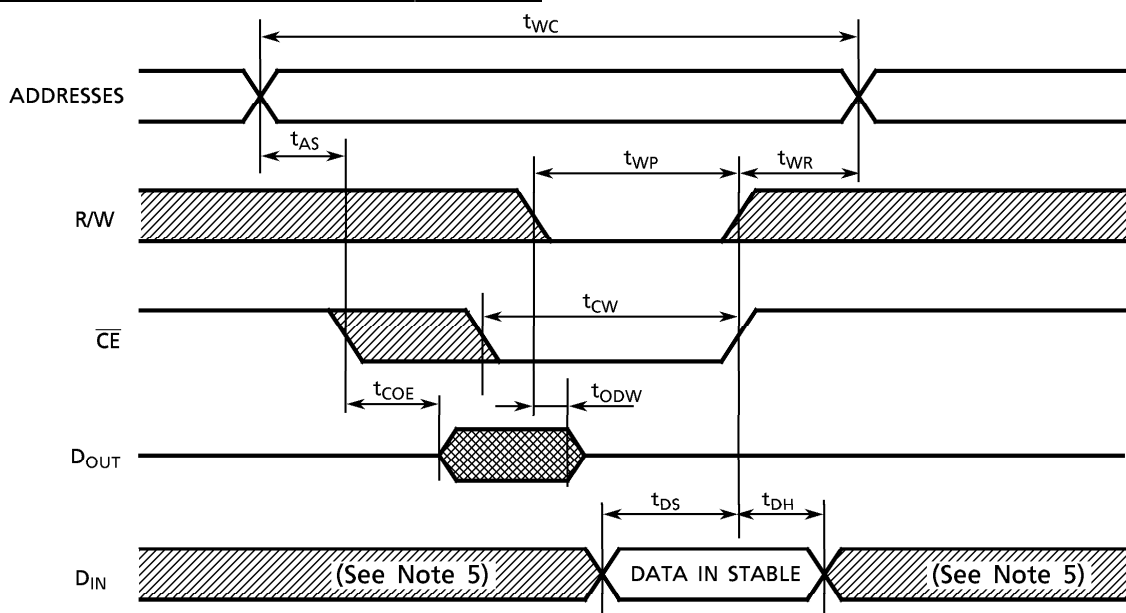
TIMING WAVEFORMS

READ CYCLE (See Note 1)



WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



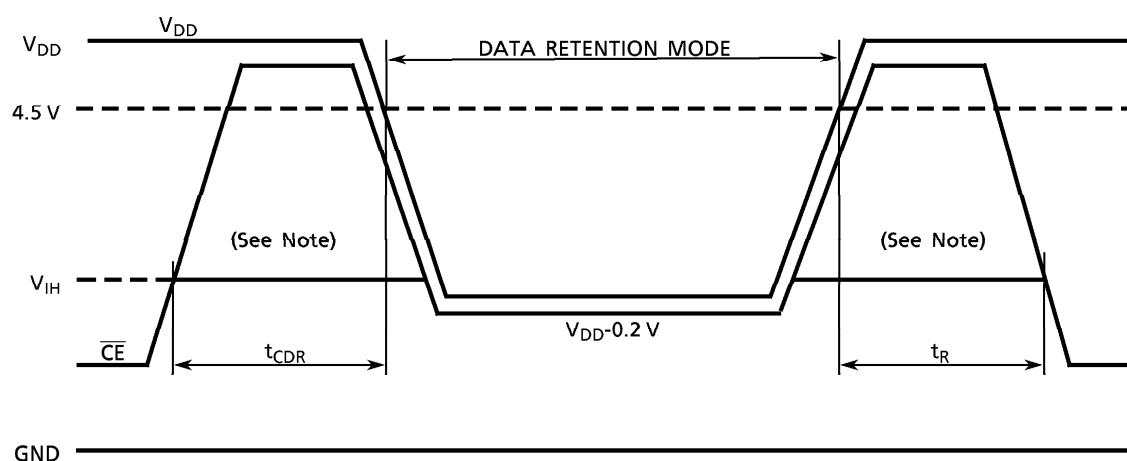
WRITE CYCLE 2 ($\overline{CE}$ CONTROLLED) (See Note 4)


- (1) R/W remains High for Read Cycle.
- (2) If $\overline{CE}$ goes coincident with or after R/W goes LOW, the output will remain at high impedance.
- (3) If $\overline{CE}$ goes HIGH coincident with or before R/W goes HIGH, the output will remain at high impedance.
- (4) IF $\overline{CE}$ is HIGH during the write cycle, the outputs will remain at high impedance.
- (5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

DATA RETENTION CHARACTERISTICS ($T_a = 0^\circ$ to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{DH}	Data Retention Supply Voltage	2.0	–	5.5	V
I_{DD2}	Standby Current	$V_{DH} = 3.3\text{ V}$	–	35*	μA
		$V_{DH} = 5.5\text{ V}$	–	60	
t_{CDR}	Chip Deselect to Data Retention Mode Time	0	–	–	nS
t_R	Recovery Time	5	–	–	mS

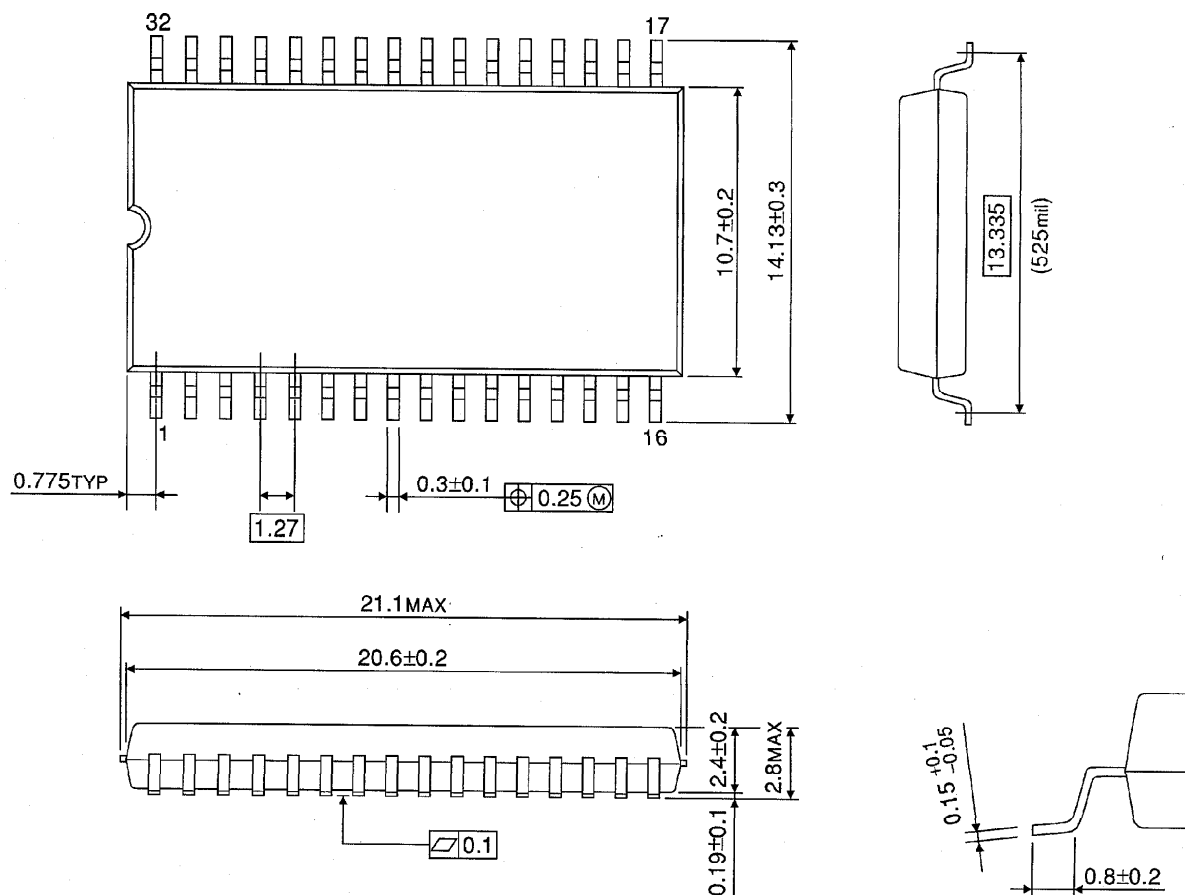
*) $8\text{ }\mu\text{A}$ (max) $T_a = 0^\circ$ to 40°C

 $\overline{\text{CE}}$ Controlled Data Retention Mode


Note: When $\overline{\text{CE}}$ is operating at the V_{IH} level (2.2V), the standby current is given by I_{DD1} during the transition of V_{DD} from 4.5 to 2.4V.

PACKAGE DIMENSIONS (SOP32-P-525-1.27)

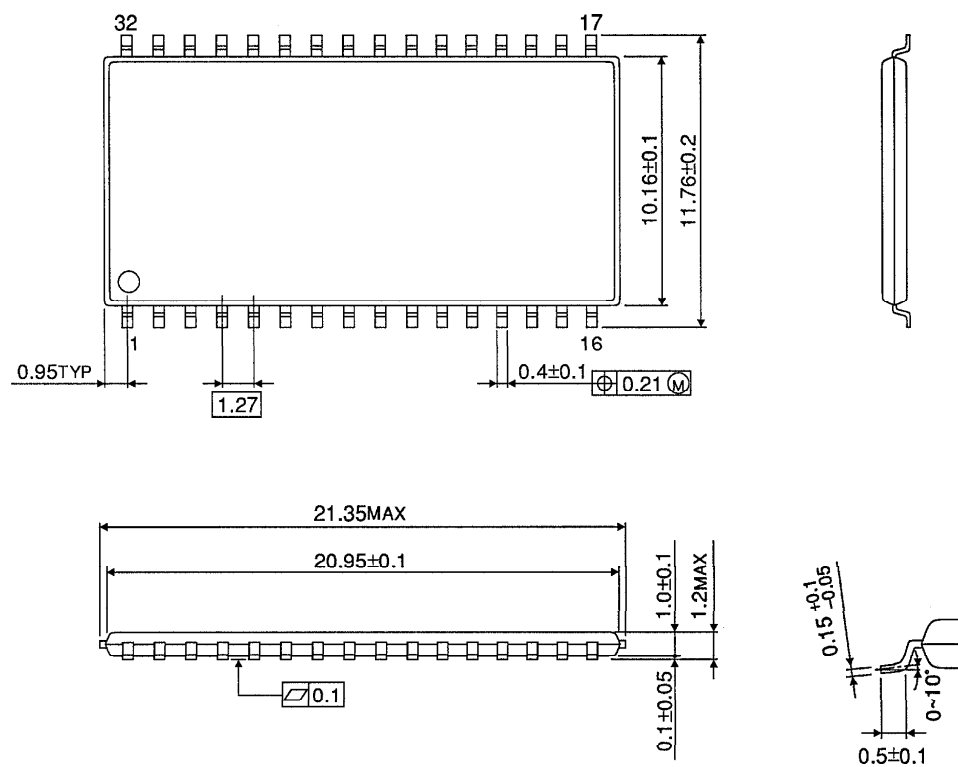
Unit in mm



Weight: 1.14 g (typ)

PACKAGE DIMENSIONS (TSOPII 32-P-400-1.27)

Unit in mm



Weight: 0.51 g (typ)